

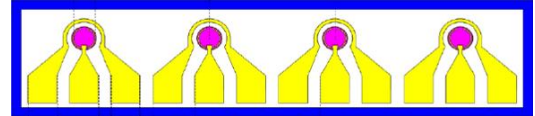


## Non-Hermetic 25Gbps GaAs PIN Photodiode 1x4 Array

Part No. PDA-85-1X4-25G

### Features

- 1x4 array bar with 250um pitch
- High responsivity at 850nm
- Optimized for fiber optic application
- Low dark current and low capacitance
- Non-hermetic design

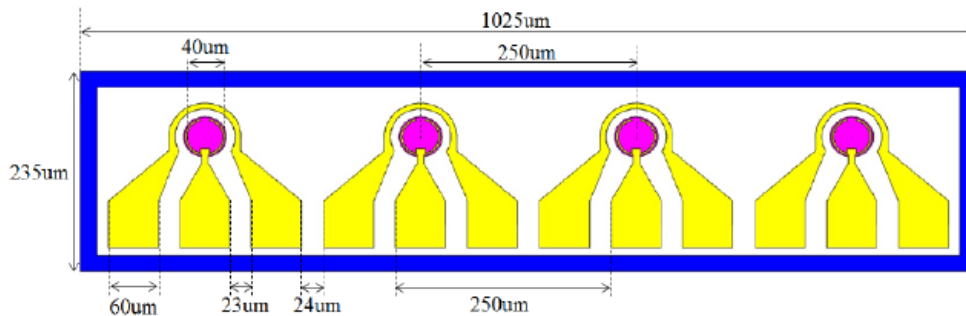


### Specifications

Absolute Maximum Ratings					
Parameters	Min.	Max.	Unit	Conditions	
Storage Temperature	-40	100	°C		
Operating Temperature	-40	85	°C		
Reverse Current		2	mA	T=25°C	
Forward Current		10	mA	T=25°C	
Reverse Voltage		20	V	T=25°C	

Electro-Optical Characteristics (T <sub>a</sub> =25°C unless otherwise stated)						
Parameters	Symbol	Min.	Typ.	Max.	Unit	Conditions
Responsivity	R	0.55	0.6		A/W	V <sub>R</sub> =2V, λ=850nm
Dark Current	I <sub>D</sub>		0.1	1.0	nA	V <sub>R</sub> =5V
Breakdown Voltage	V <sub>B</sub>	30			V	I <sub>F</sub> =10uA
Capacitance	C		0.1	0.12	pF	V <sub>R</sub> =2V, f=1MHz
Bandwidth	BW		17		GHz	V <sub>R</sub> =2V

### Outline Dimensions (unit: mm)

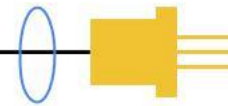


- Chip size is typical 1025um x 235um.
- Chip thickness is 150±12.5um.
- Sensitive area is typical 40um in diameter.

**Lasermate Group, Inc.**

19608 Camino De Rosa, Walnut, CA 91789, USA

Tel: (909)718-0999 | Fax: (909)718-0998 | E-mail: [info@lasermate.com](mailto:info@lasermate.com) | URL: <http://www.lasermate.com>



## Typical Characteristics

Fig. 1 Typical Dark Current and Forward Current

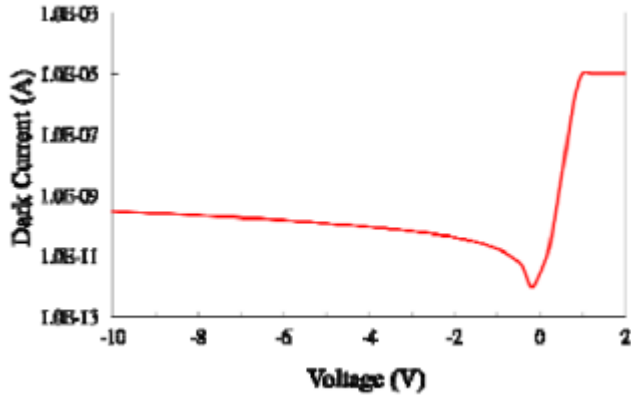


Fig. 2 Typical Photo Current

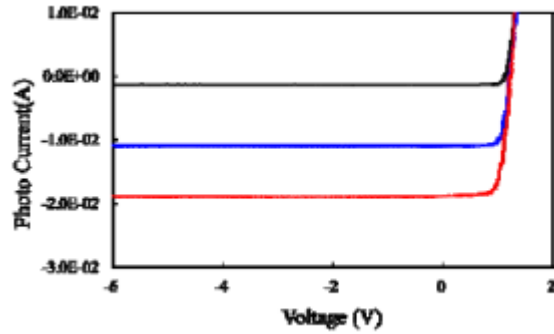


Fig. 3 Typical Breakdown Curve

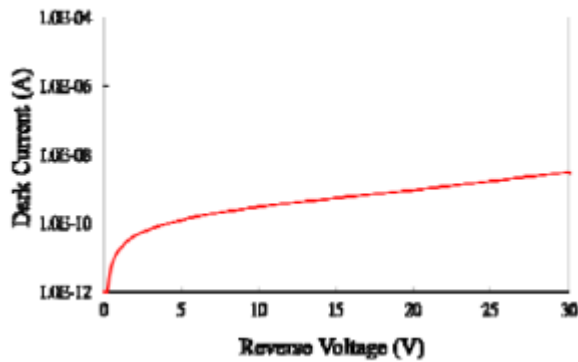
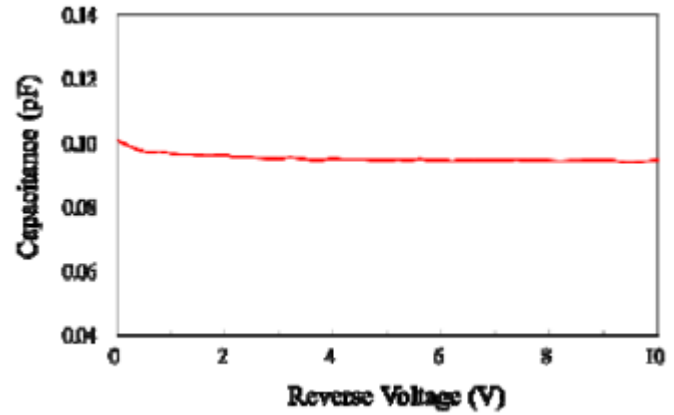


Fig. 4 Typical C-V Curve



Note: Specifications are subject to change without notice.